

2SB954, 2SB954A

Silicon PNP Epitaxial Planar Type

Power Amplifier

■ Features

- High DC current gain (h_{FE}) and good linearity
- Low collector-emitter saturation voltage ($V_{CE(sat)}$)
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	2SB954	-60	V
	2SB954A	-80	
Collector-emitter voltage	2SB954	-60	V
	2SB954A	-80	
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-2	A
Collector current	I_C	-1	A
Collector power dissipation	$T_c=25^\circ\text{C}$	30	W
	$T_a=25^\circ\text{C}$	2	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	2SB954	$V_{CE} = -30\text{ V}, I_B = 0$			-300	μA
	2SB954A	$V_{CE} = -60\text{ V}, I_B = 0$			-300	
Collector cutoff current	2SB954	$V_{CE} = -60\text{ V}, V_{BE} = 0$			-200	μA
	2SB954A	$V_{CE} = -80\text{ V}, V_{BE} = 0$			-200	
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-1	mA
Collector-emitter voltage	2SB954	$I_C = -30\text{ mA}, I_B = 0$	-60			V
	2SB954A		-80			
DC current gain	h_{FE1}^*	$V_{CE} = -4\text{ V}, I_C = -0.2\text{ A}$	40		450	
	h_{FE2}	$V_{CE} = -4\text{ V}, I_C = -1\text{ A}$	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1\text{ A}, I_B = -0.125\text{ A}$			-1	V
Base-emitter saturation voltage	V_{BE}	$V_{CE} = -4\text{ V}, I_C = -1\text{ A}$			-1.3	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -0.2\text{ A}, f = 10\text{ MHz}$		30		MHz
Turn-on time	t_{on}	$I_C = -1\text{ A}, I_{B1} = -0.1\text{ A}, I_{B2} = 0.1\text{ A}, V_{CC} = -50\text{ V}$		0.5		μs
Storage time	t_{stg}			1.2		μs
Collector current fall time	t_f			0.3		μs

* h_{FE1} Classifications

Class	R	Q	P
h_{FE1}	40 ~ 90	70 ~ 150	120 ~ 250

■ Package Dimensions



